

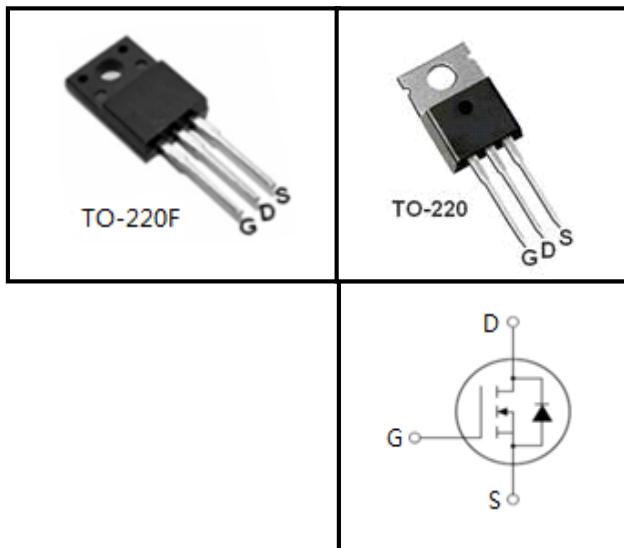
## 600V N-Channel MOSFET

### FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

### APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , unless otherwise noted

Parameter	Symbol	Value		Unit
		TO-220F/TO-220		
Drain-Source Voltage ( $V_{GS} = 0\text{V}$ )	$V_{DSS}$	600		V
Continuous Drain Current	$I_D$	20		A
Pulsed Drain Current (note1)	$I_{DM}$	80		A
Gate-Source Voltage	$V_{GSS}$	$\pm 30$		V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	1280		mJ
Avalanche Current (note1)	$I_{AR}$	16		A
Repetitive Avalanche Energy (note1)	$E_{AR}$	90		mJ
Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_D$	120		W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150		$^\circ\text{C}$

### Thermal Resistance

Parameter	Symbol	Value		Unit
		TO-220F/TO-220		
Thermal Resistance, Junction-to-Case	$R_{thJC}$	1.04		
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	62.5		$^\circ\text{C/W}$

**Specifications  $T_J = 25^\circ\text{C}$ , unless otherwise noted**

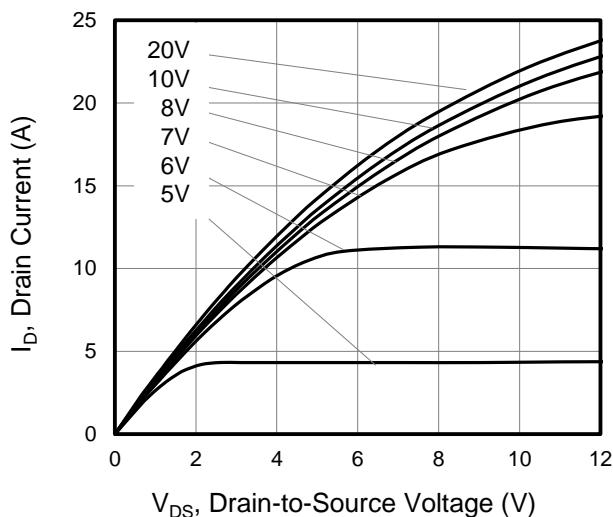
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	600	--	--	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}} = 600\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 25^\circ\text{C}$	--	--	1	$\mu\text{A}$
Gate-Source Leakage	$I_{\text{GSS}}$	$V_{\text{GS}} = \pm 30\text{V}$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 10\text{A}$	--	0.32	0.40	$\Omega$
<b>Dynamic</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 25\text{V}, f = 1.0\text{MHz}$	--	2978	--	pF
Output Capacitance	$C_{\text{oss}}$		--	291	--	
Reverse Transfer Capacitance	$C_{\text{rss}}$		--	40	--	
Total Gate Charge	$Q_g$	$V_{\text{DD}} = 480\text{V}, I_D = 20\text{A}, V_{\text{GS}} = 10\text{V}$	--	80	--	nC
Gate-Source Charge	$Q_{\text{gs}}$		--	12	--	
Gate-Drain Charge	$Q_{\text{gd}}$		--	34	--	
Turn-on Delay Time	$t_{d(\text{on})}$	$V_{\text{DD}} = 250\text{V}, I_D = 20\text{A}, R_G = 25 \Omega$	--	37	--	ns
Turn-on Rise Time	$t_r$		--	66	--	
Turn-off Delay Time	$t_{d(\text{off})}$		--	175	--	
Turn-off Fall Time	$t_f$		--	84	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	20	A
Pulsed Diode Forward Current	$I_{\text{SM}}$		--	--	80	
Body Diode Voltage	$V_{\text{SD}}$	$T_J = 25^\circ\text{C}, I_{\text{SD}} = 20\text{A}, V_{\text{GS}} = 0\text{V}$	--	--	1.4	V
Reverse Recovery Time	$t_{rr}$	$V_{\text{GS}} = 0\text{V}, I_S = 20\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	--	450	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	7.1	--	$\mu\text{C}$

**Notes**

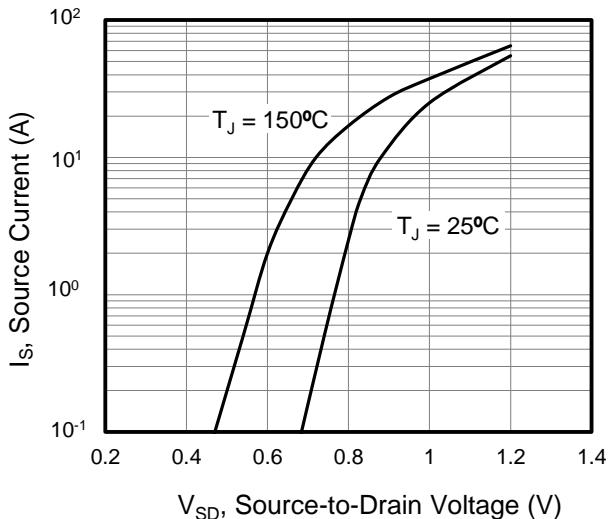
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $I_{AS} = 16\text{A}, V_{DD} = 50\text{V}, R_G = 25 \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 1\%$

**Typical Characteristics**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

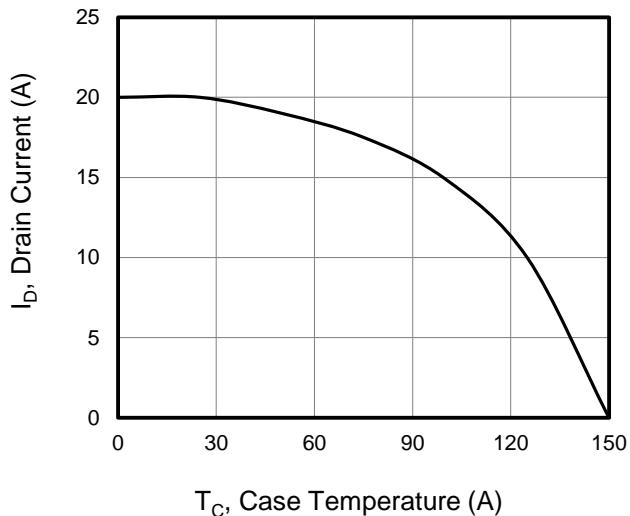
**Figure 1. Output Characteristics ( $T_J = 25^\circ\text{C}$ )**



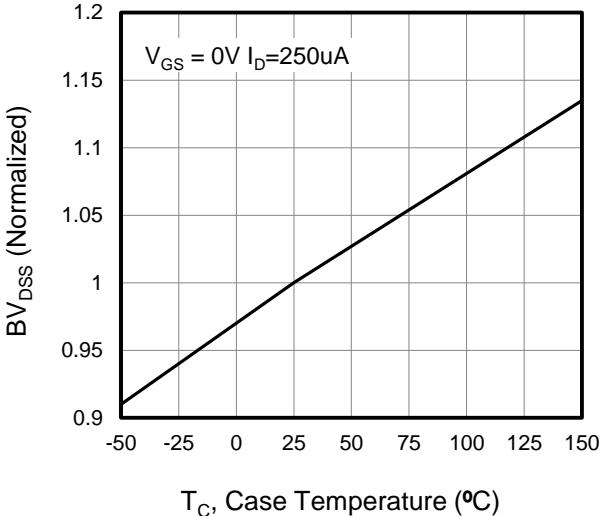
**Figure 2. Body Diode Forward Voltage**



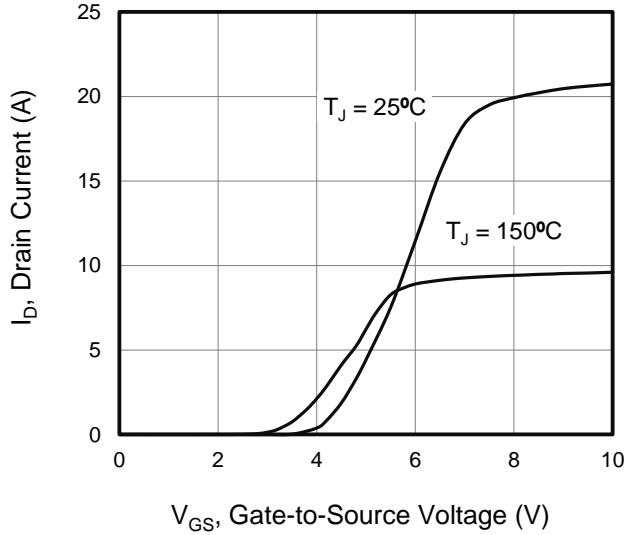
**Figure 3. Drain Current vs. Temperature**



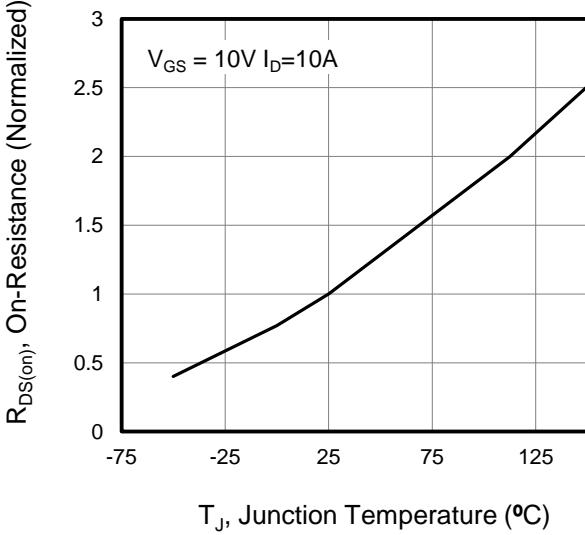
**Figure 4.  $BV_{DSS}$  Variation vs. Temperature**



**Figure 5. Transfer Characteristics**

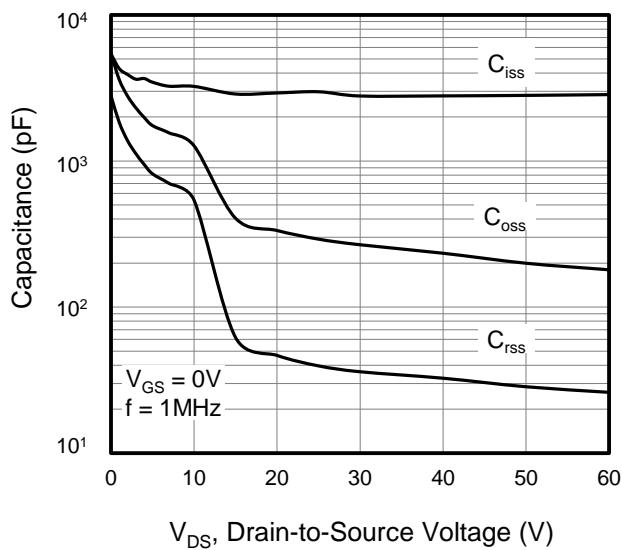


**Figure 6. On-Resistance vs. Temperature**

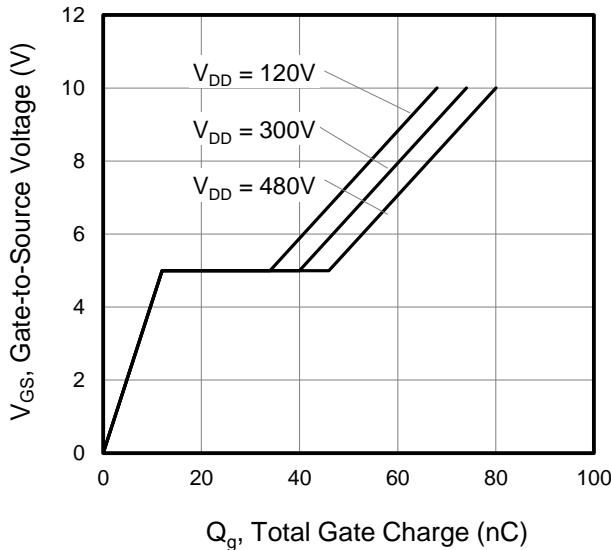


**Typical Characteristics**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

**Figure 7. Capacitance**

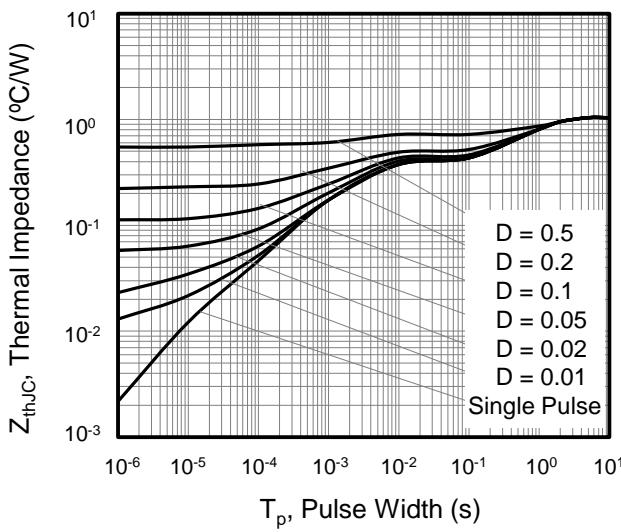


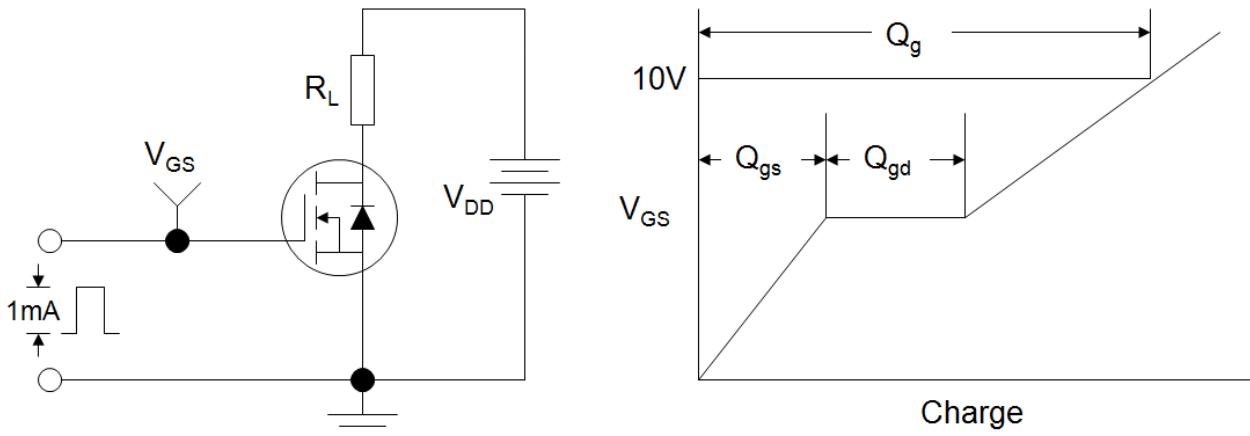
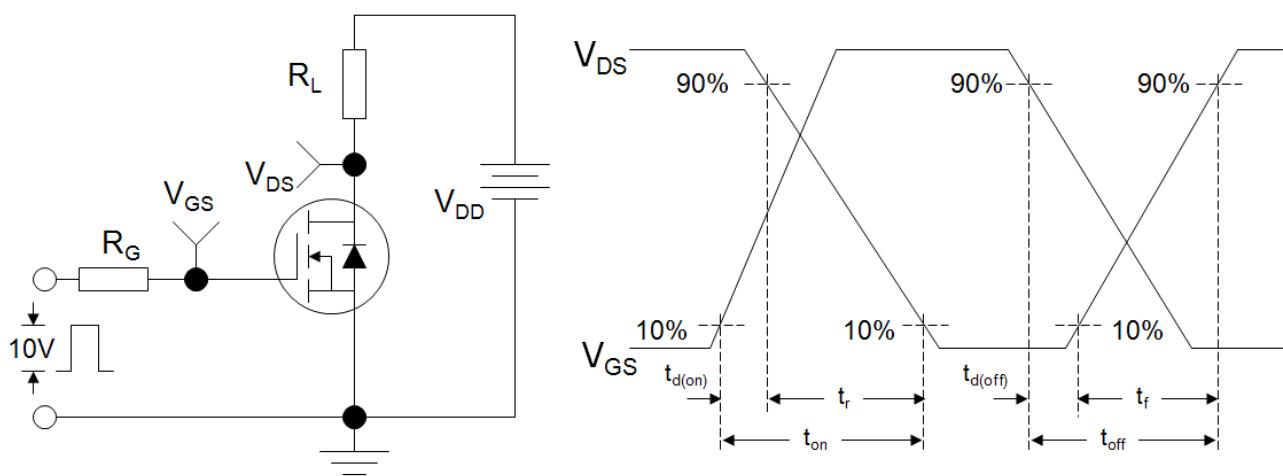
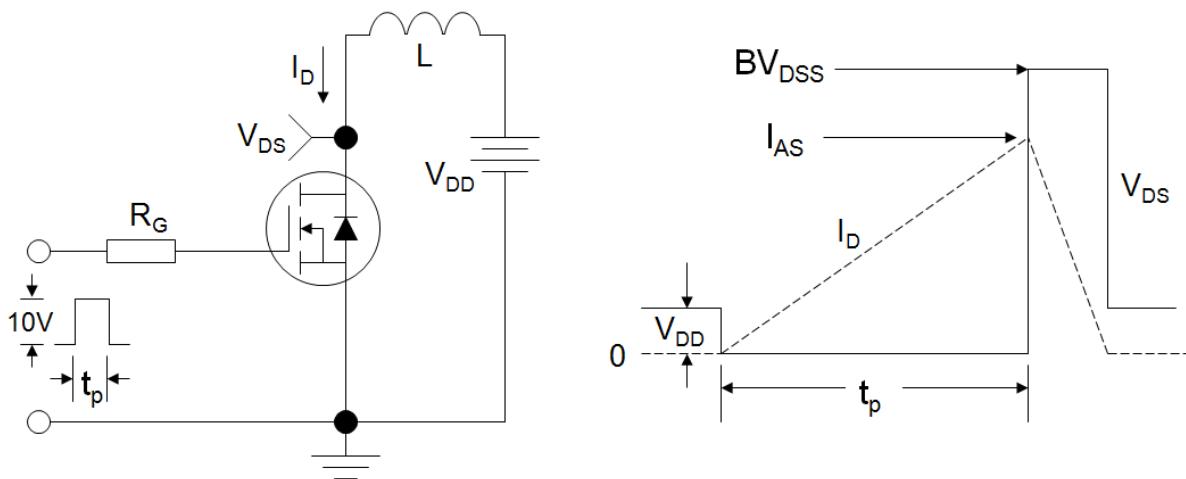
**Figure 8. Gate Charge**



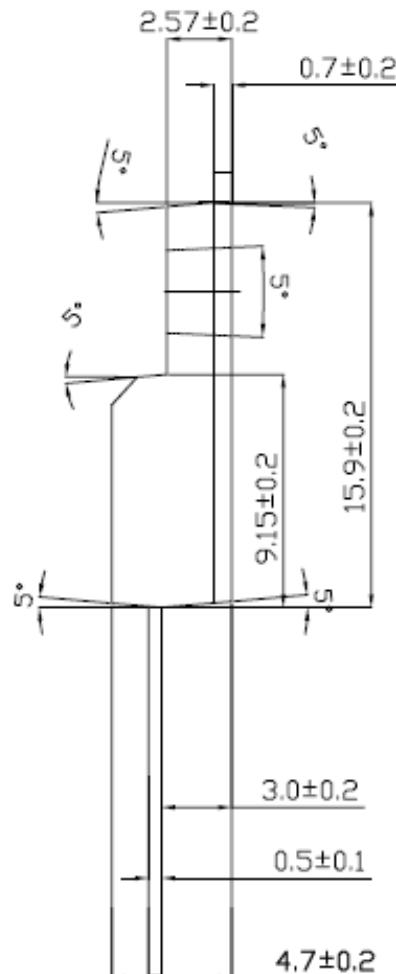
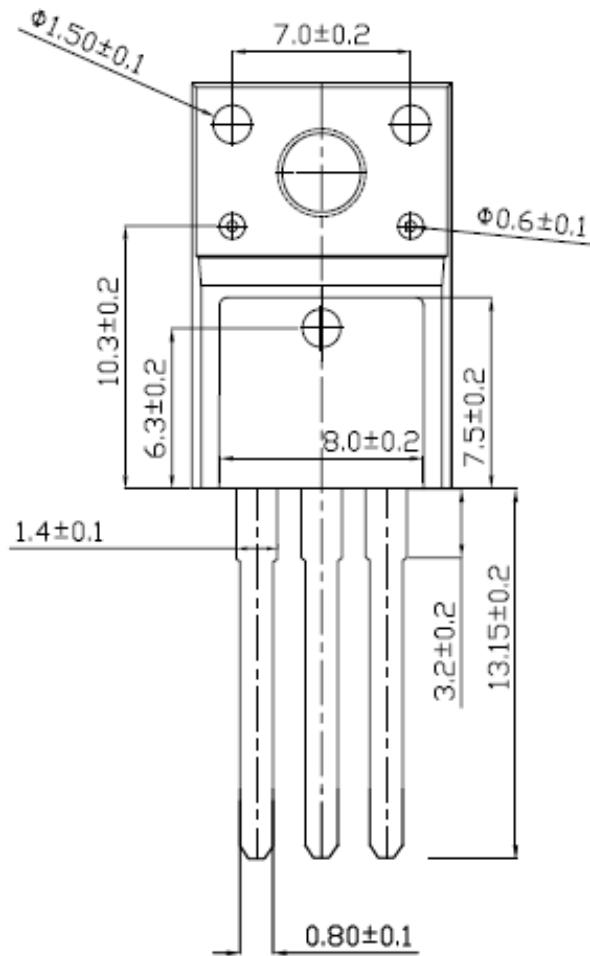
**Figure 9. Transient Thermal Impedance**

TO-220F

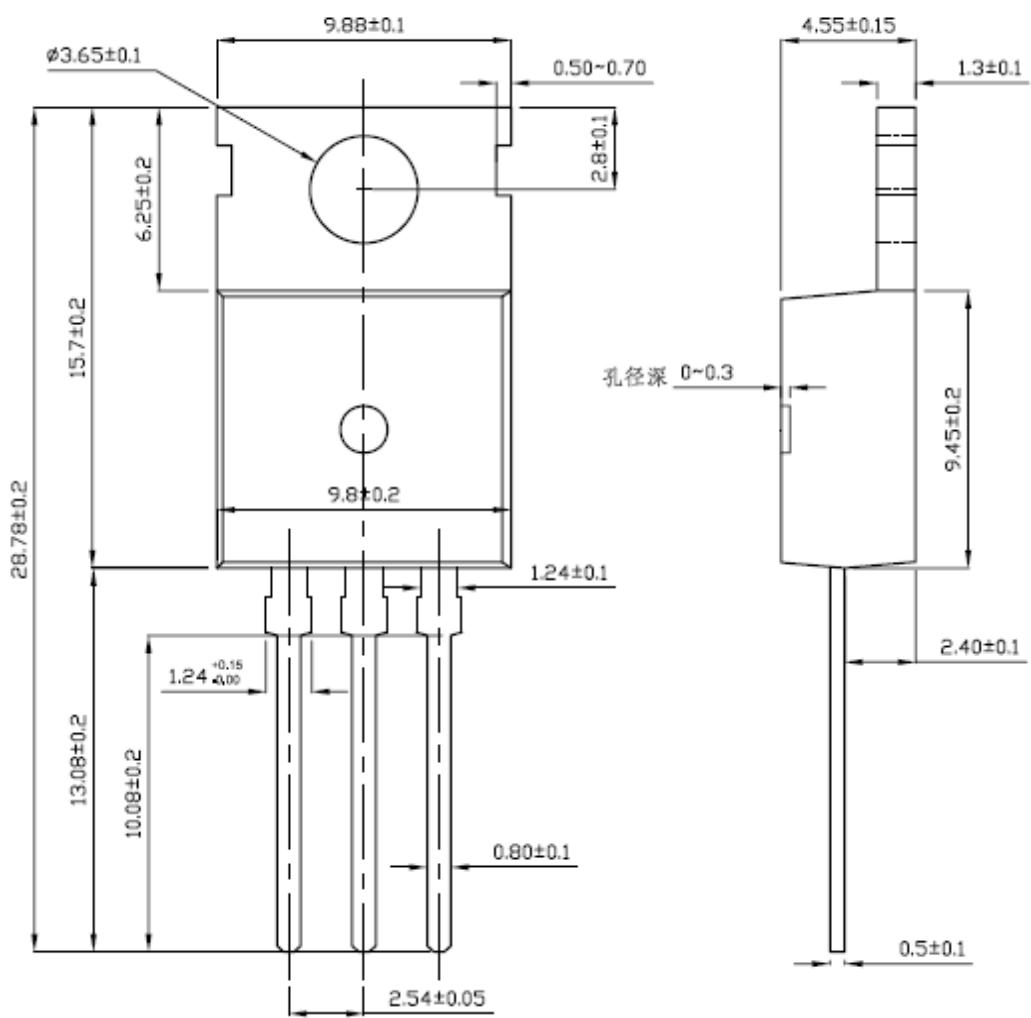


**Figure A: Gate Charge Test Circuit and Waveform**

**Figure B: Resistive Switching Test Circuit and Waveform**

**Figure C: Unclamped Inductive Switching Test Circuit and Waveform**


## TO-220F



## TO-220



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